NSN 5961-01-053-3316

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View Online at https://aerobasegroup.com/nsn/5961-01-053-3316

Inclosure Material:

Ceramic

Overall Length:

Between 0.890 inches and 0.910 inches

Overall Height:

0.240 inches

Overall Width:

Between 0.376 inches and 0.410 inches

End Application:

An/fps-115

Mounting Facility Quantity:

2

Internal Configuration:

Junction contact

Electrode Internally-electrically Connected To Case:

Base

Mounting Method:

Unthreaded hole

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

65.0 collector to base voltage/static/emitter open and 25.0 collector to emitter voltage/static/base open and 4.0 emitter to base voltage, instantaneous

Current Rating Per Characteristic:

10.00 amperes source cutoff current

Power Rating Per Characteristic:

80.0 watts small-signal input power, common-collector absolute

Maximum Operating Tempurature Per Measurement Point:

200.0 degrees celsius junction

Special Features:

T.O. 31p6-2fps115-62; n/h/a rf amplifier; junction pattern arrangement: npn

Precious Material And Location:

Plated leads gold

Precious Material:

Gold

Test Data Document:

49956-914509 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.;

excludes any specification, standard or other document that may be referenced in a basic governing drawing)

Terminal Type And Quantity:

2 ribbon and 1 case

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

A110a0

